

Surface Mount

Thyristor Surge Protective Devices

TSP0080SB-TSP4200SB

TSP0080SB – TSP4200SB Series are designed to protect broadband equipment such as modems, line card, CPE and DSL from damaging over-voltage transients.

The series provides a surface mount solution that enables equipment to comply with global regulatory standards.

FEATURES

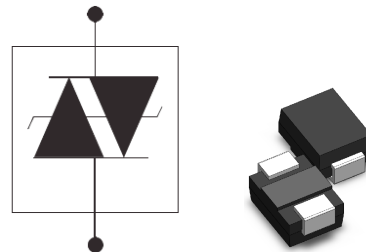
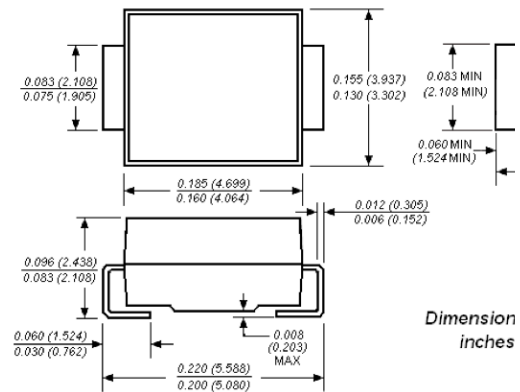
- Low voltage overshoot
- Low on-state voltage
- Does not degrade surge capability after multiple surge events within limit
- Fails short circuit when surged in excess of ratings
- Low Capacitance

MECHANICAL DATA

Case: SMB Molded plastic

Main applications

- TIA-968-A
- ITU K.20/21 Enhanced level
- ITU K.20/21 Basic Level
- GR 1089 Inter building
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- IEC 6100-4-5
- YD/T 1082 YD/T 993 YD/T 950



Absolute Ratings (T _{amb} =25°C)				
Symbol	Parameter		Value	Unit
T _s	Storage temperature range		-55 to +150	°C
T _j	Maximum junction temperature		150	°C
I _{PP}	Repetitive peak pulse current	10/1000μs	75	A
		10/560μs	100	
		10/160μs	150	
		8/20μs	250	
		2/10μs	250	
I _{TSM}	Non repetitive surge peak on-state current (sinusoidal)	t=1s	8	A

Electrical Parameters

Symbol	Parameter
V _{RM}	Stand-off voltage
V _{BR}	Breakdown voltage
V _{BO}	Breakover voltage
I _{RM}	Leakage current
I _{PP}	Peak pulse current
I _{BO}	Breakover current
I _H	Holding current
V _R	Continuous reverse voltage
I _R	Leakage current at V _R
C ₀	Capacitance

Electrical Characteristics (25°C)

	V _{RM}	I _{RM}	V _{BO}	I _{BO}	V _T	I _T	C ₀	I _H
	Min		Max.	Max.	Max.		Max.	Min.
TSP0080SB	V	μA	V	mA	V	A	pF	mA
	6	2	15	800	2	1	80	50
TSP4200SB	390	5	500	800	2.2	1	25	150

• Characteristic Curves

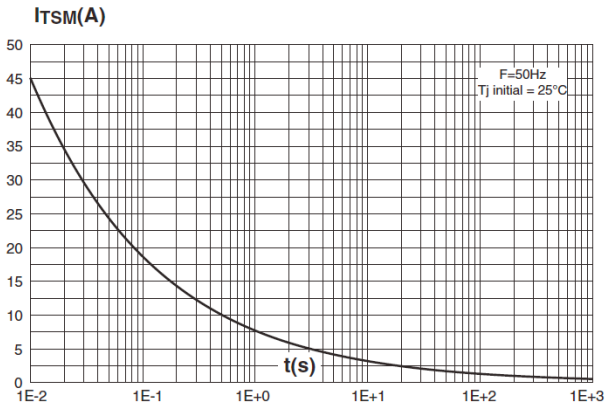


Figure 1. Non repetitive surge peak on-state current versus overload duration

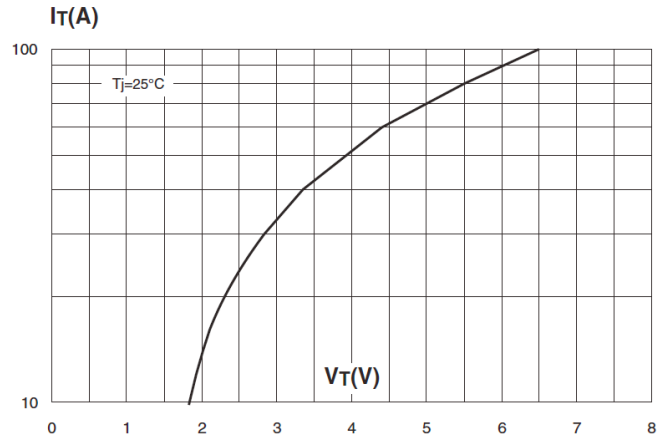


Figure 2. On-state voltage versus on-state current (typical values)

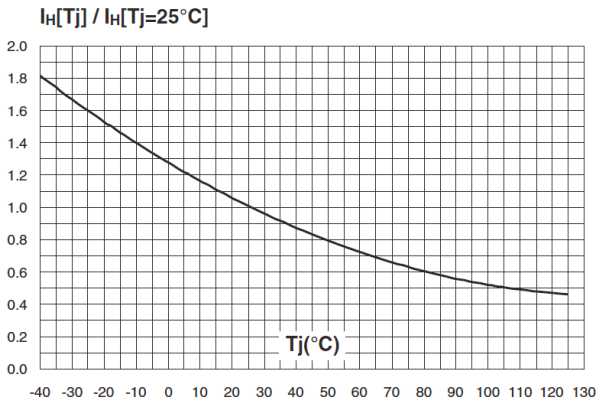


Figure 3. Relative variation of holding current versus junction temperature

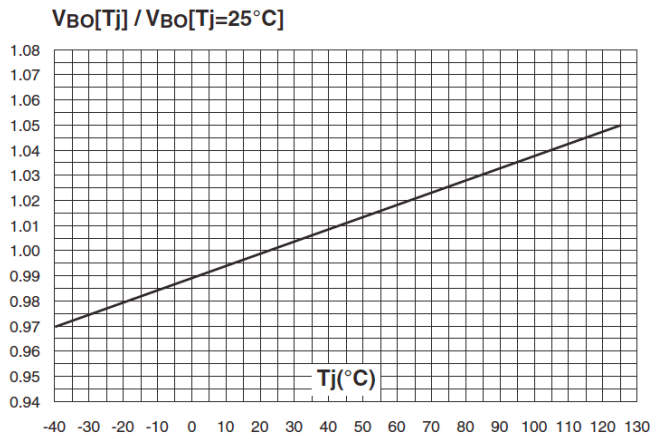


Figure 4. Relative variation of break over voltage versus junction temperature

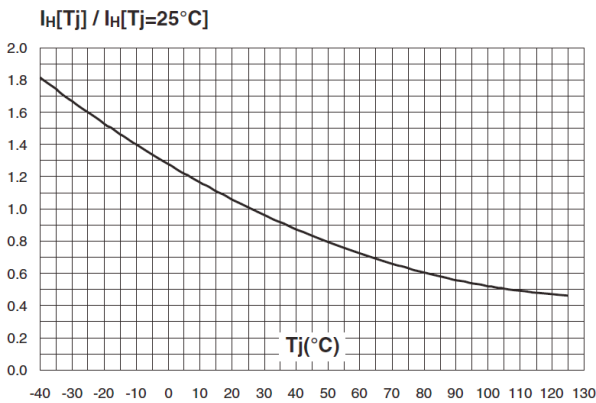


Figure 5. Relative variation of holding current versus junction temperature

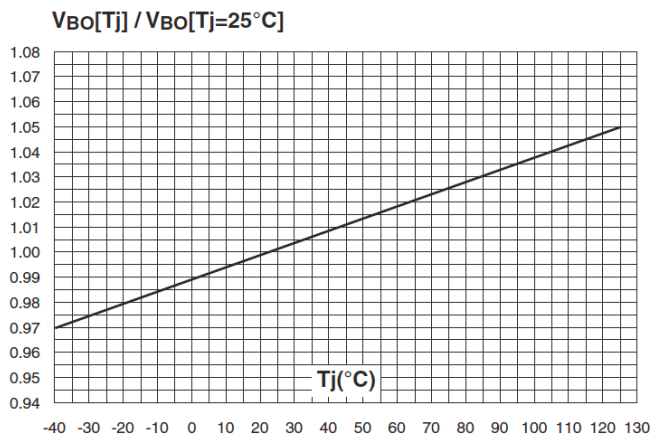


Figure 6. Relative variation of break over voltage versus junction temperature

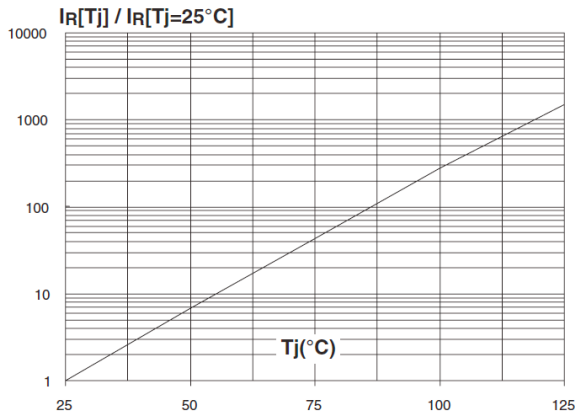


Figure 7. Relative variation of leakage current versus reverse voltage applied (typical values)

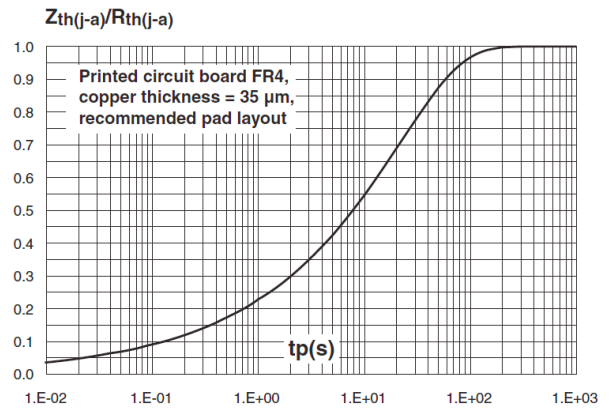


Figure 8. Variation of thermal impedance junction to ambient versus pulse duration